
LEDPUF: Stability-Guaranteed Physical Unclonable Functions through Locally Enhanced Defectivity

Wei-Che Wang, Prof. Puneet Gupta
Dr. Yair Yona, and Prof. Suhas Diggavi
UCLA Electrical Engineering

Limitations of Silicon PUFs

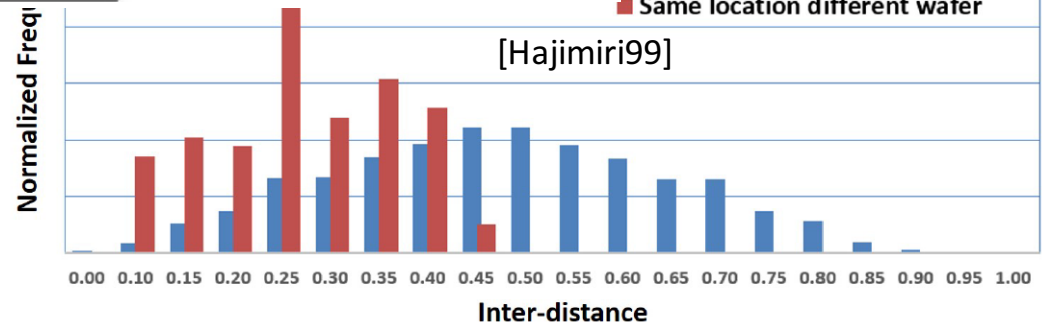
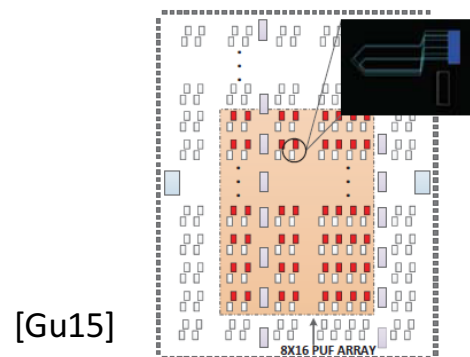
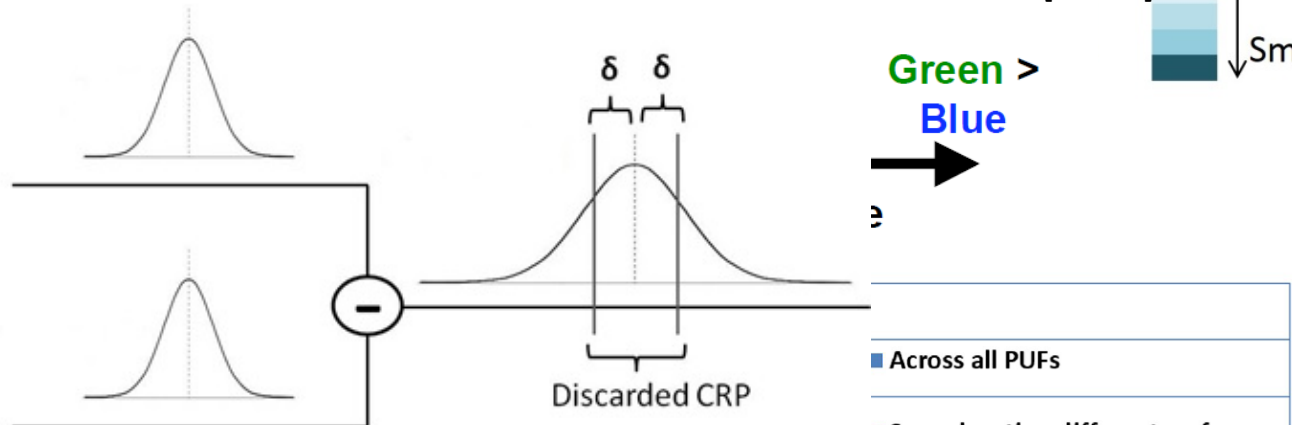
- **Stability**

- Environmental fluctuations
- Measurement noise



- **Uniqueness**

- Randomness
- Routing consistency



Locally Enhanced Hard Defectivity (LED)

- **Hard defectivity**

- Permanent defectivity
- No parametric variations

Stable!

- **Locally enhanced randomness**

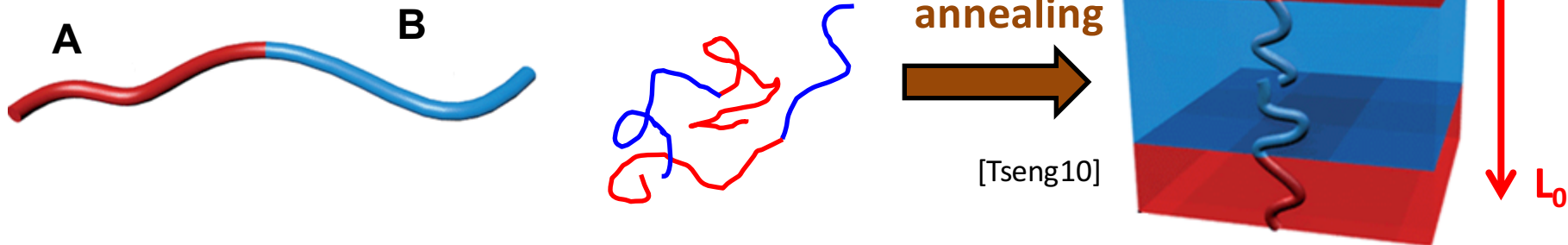
- No impact (from hard defectivity) to other parts of the chip
- Through physical design
- Compatible with circuit design flow

Unique!

Directed Self Assembly

- **Directed Self Assembly (DSA)**

- Promising patterning candidate for <7nm
- Block copolymer phase separation

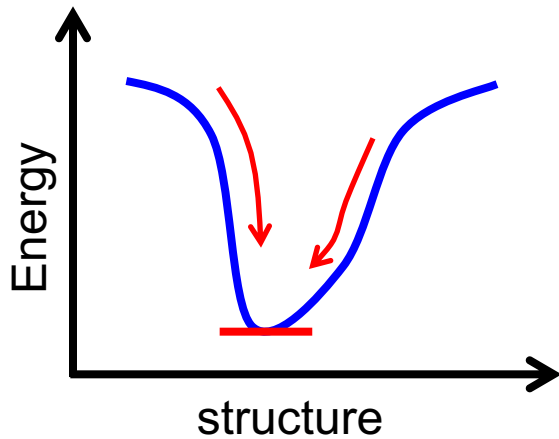


- Guiding template interaction

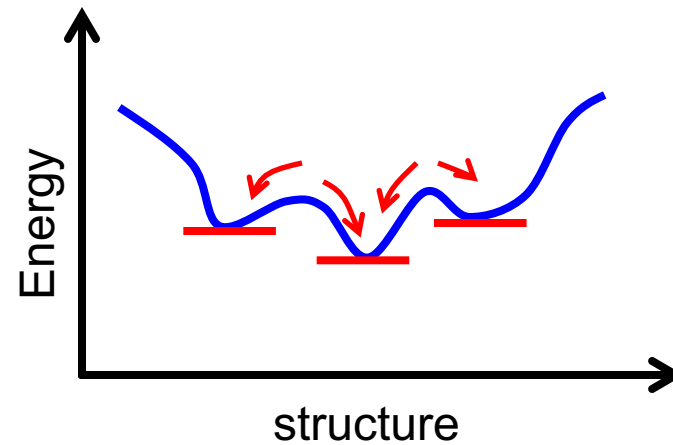
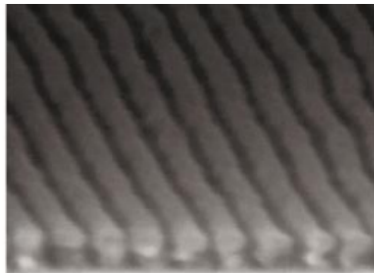


Minimum Energy State

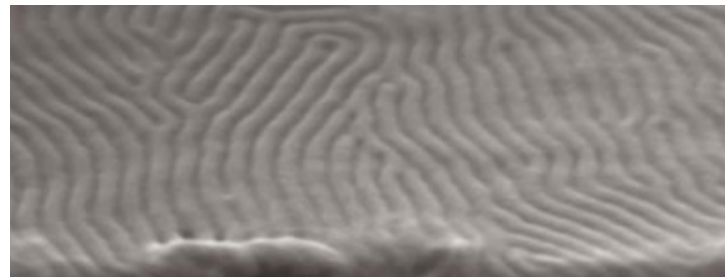
- One of the minimum energy states is reached



Template width $\sim L_0$



Template width $\gg L_0$



[Kim03]

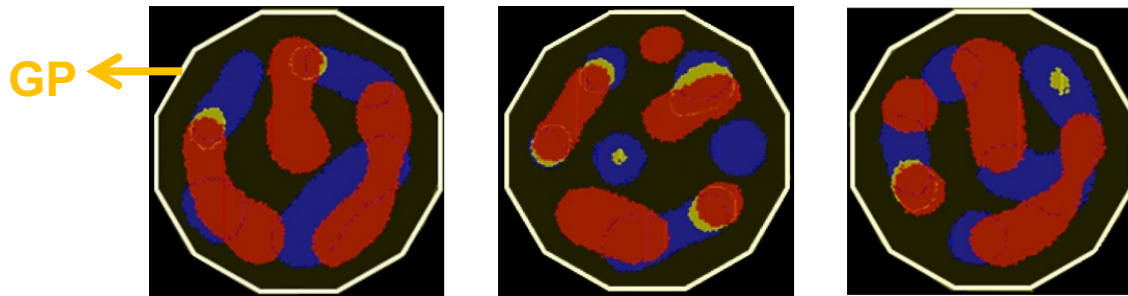
ITRS Roadmap

Table 1: Key targets and challenges for implementation of new patterning options.

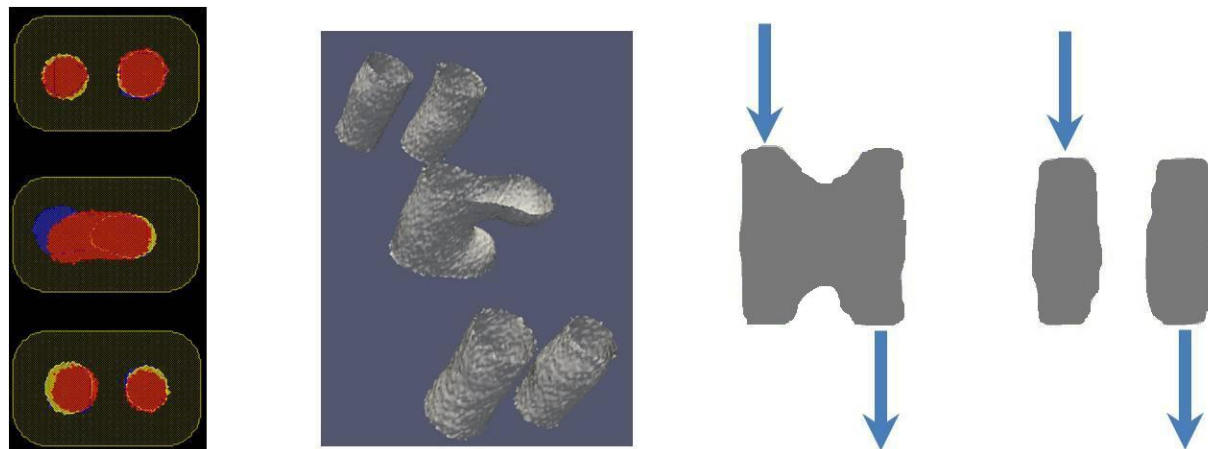
Next-generation technology	First possible use in mfg	Feature type	Device type	Key challenges	Required date for decision making
Multiple patterning extension	2019	Sub-10-nm hp fins in finFETs	'5-nm' node logic	<ul style="list-style-type: none"> - Printing and overlay of cut levels - Cost due to many masks 	2017
EUV	2017 2018	22 nm to 26 nm hp CH/cut levels 16 nm to 20 nm hp LS	'10=nm' node logic extension, '7-nm' node logic, 19-nm DRAM	<ul style="list-style-type: none"> - Enough throughput - Defects from mask - Resist sensitivity and roughness 	2015
Nanoimprint	2016	14-nm hp LS	Flash memory	<ul style="list-style-type: none"> - Detectivity - Overlay - Throughput 	2015
DSA (for pitch multiplication)	2017 2018	Contact holes/cut levels	DRAM logic	<ul style="list-style-type: none"> - Template infrastructure - Detectivity - Pattern placement - Design 	2015
Maskless lithography (ML)	2018	Contact holes/cut levels	'7-nm' node logic	<ul style="list-style-type: none"> - Throughput - Demonstrated - Multibeam tool 	2016

DSA Randomness Extraction

- With a large guiding template, random interactions begin to dominate the assembly process

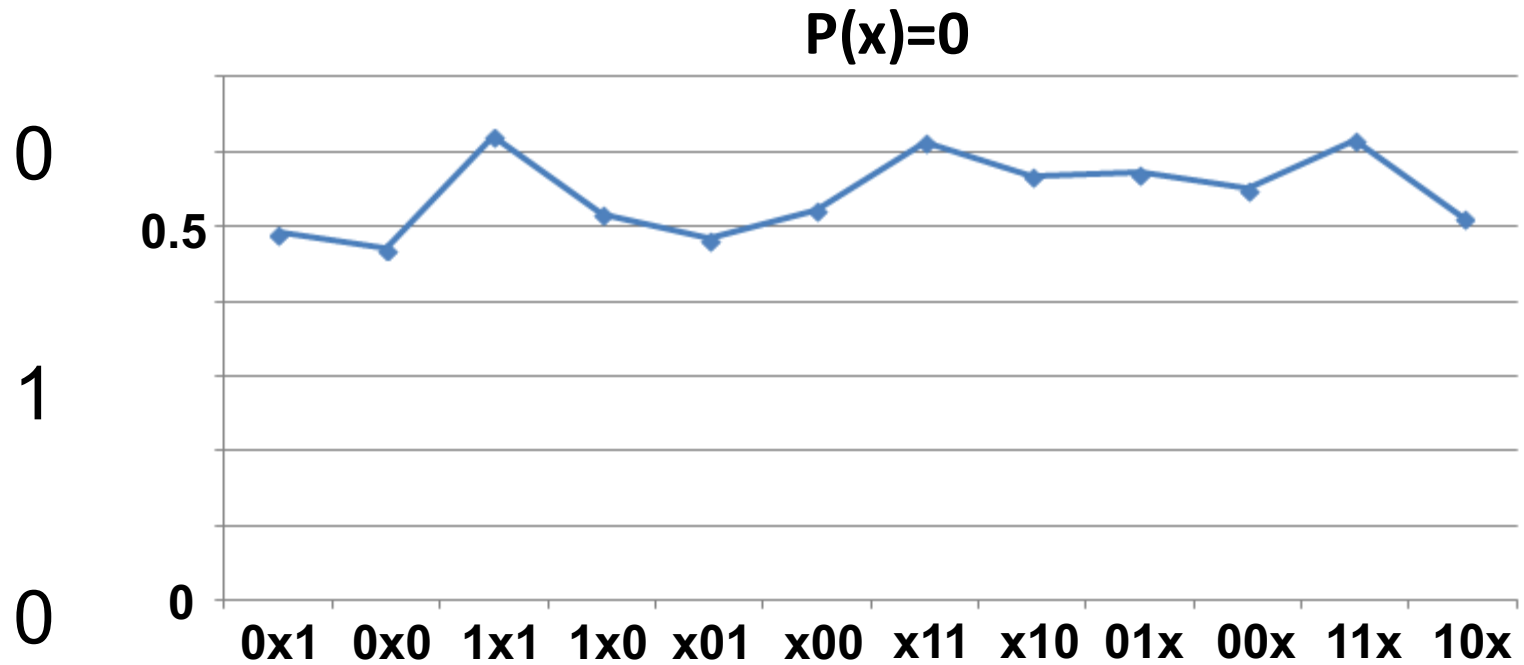
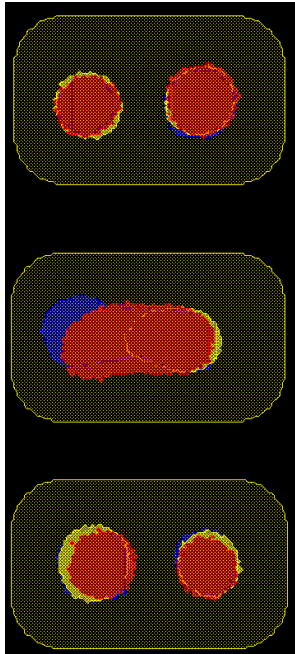


- The guiding shape is designed so that two vias are connected with certain probability



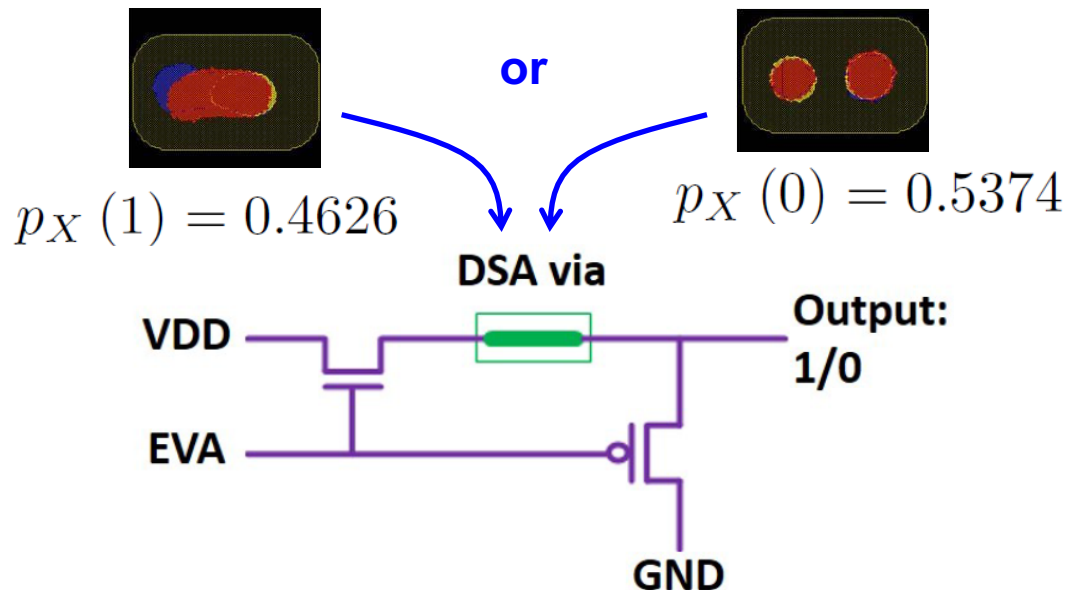
Simulation Result

- **3x500 simulations**
 - zero: 53.73%
 - one: 46.26%
- **Bits are independent**



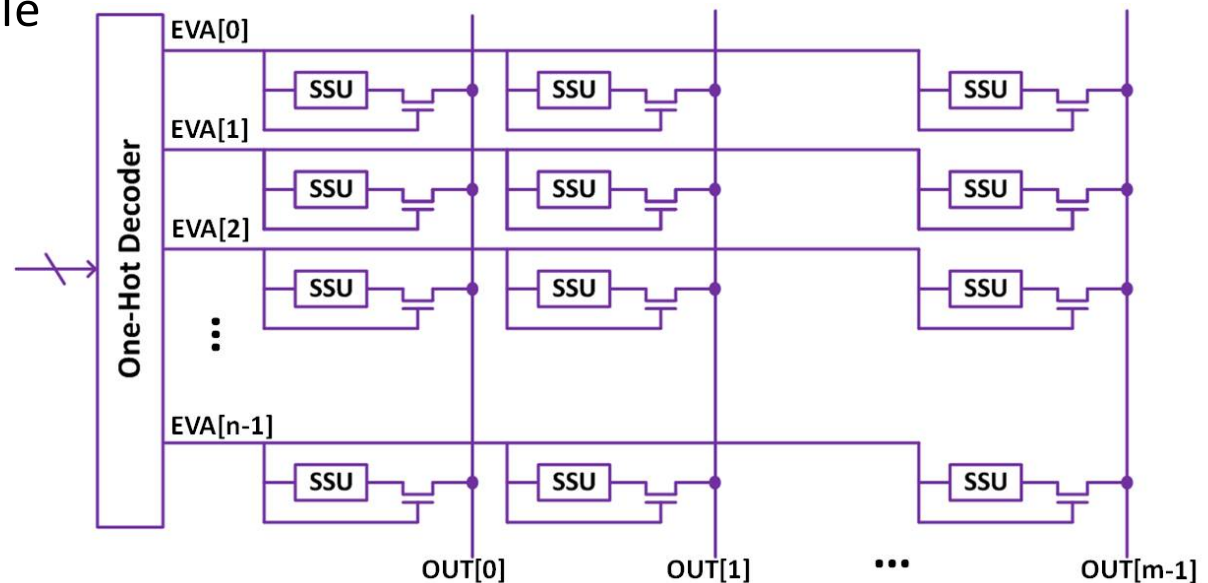
Stable Signal Unit

- A Stable Signal Unit (SSU) is constructed from a pair of DSA vias and two transistors
- When EVA. is high
 - DSA defective connection is formed \rightarrow Output is VDD (logic one)
 - DSA defective connection is not formed \rightarrow Output is GND (logic zero)



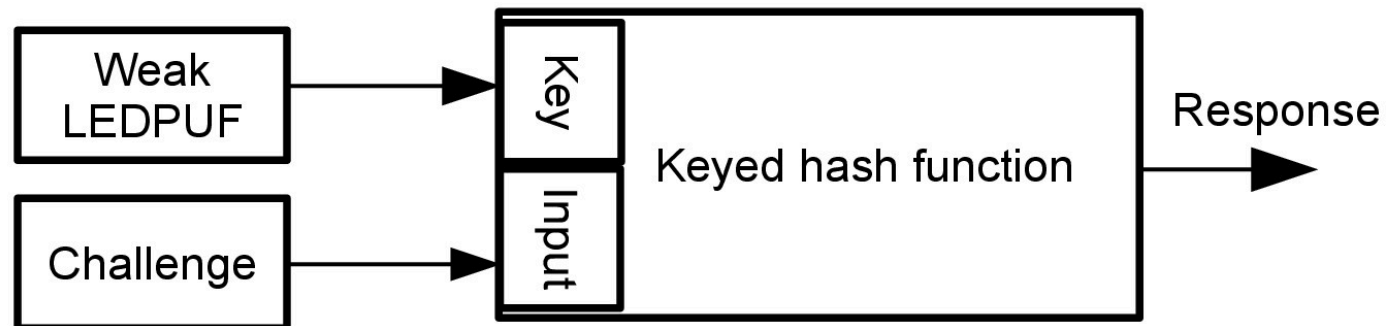
Weak LEDPUF

- A weak LEDPUF is constructed by arranging SSUs in arrays
 - **Challenge:** $\log(n)$ bits
 - **Response:** m bits
- Compared with SRAM PUF
 - More resistant to attacks
 - Completely stable



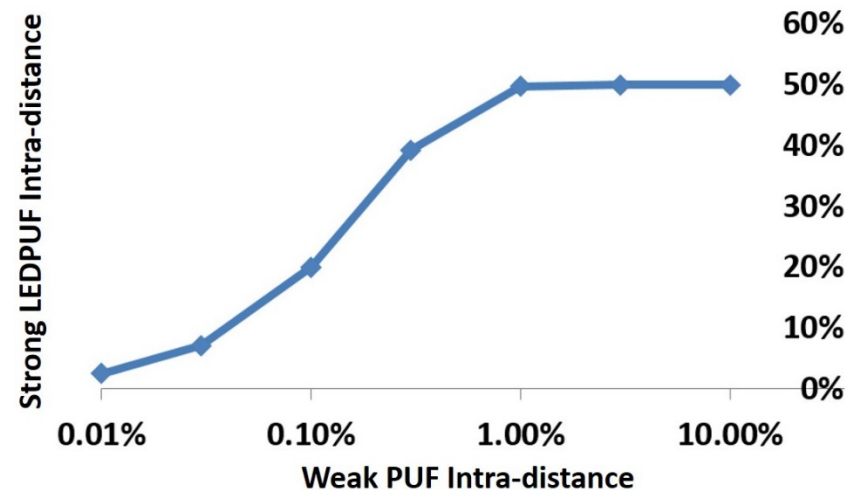
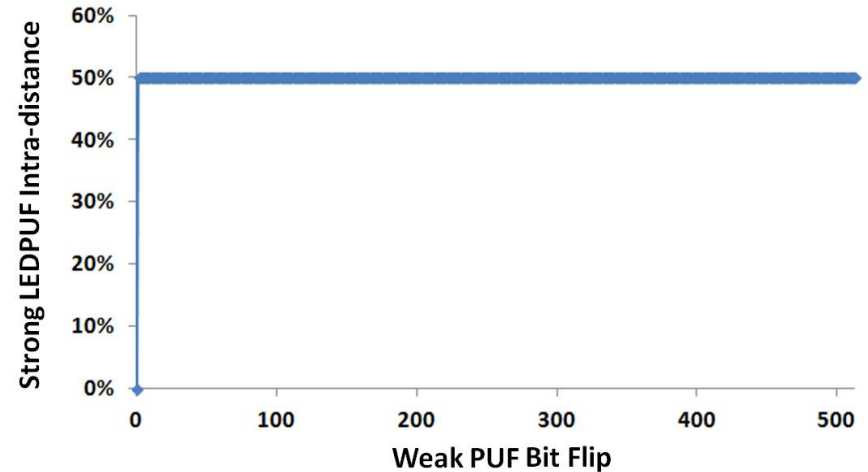
Strong LEDPUF

- A strong LEDPUF is composed of **HMAC-SHA-256** and keys from a **weak LEDPUF**
 - Completely stable requirement for the cryptographic hash
 - 2x256 bits from the stable weak LEDPUF (Initial Vectors)
 - **Challenge:** *any number of bits*
 - **Response:** 256 bits
- Compared with an Arbiter PUF
 - No efficient attacks to cryptographic hash functions
 - Completely stable



Weak LEDPUF Stability Requirement

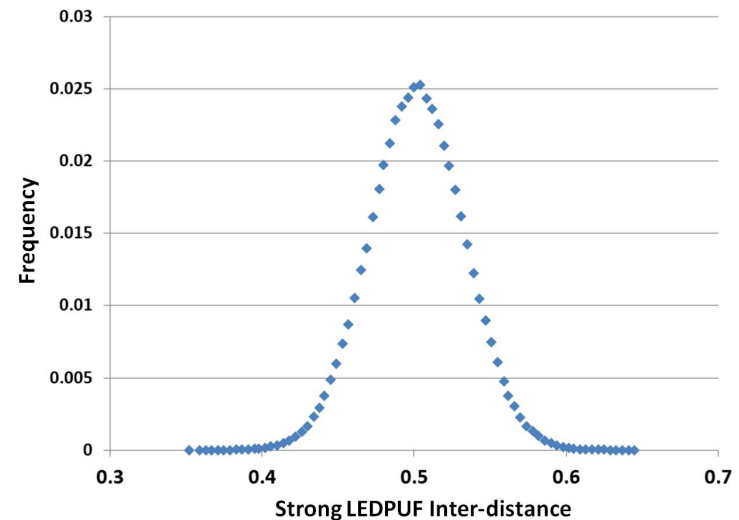
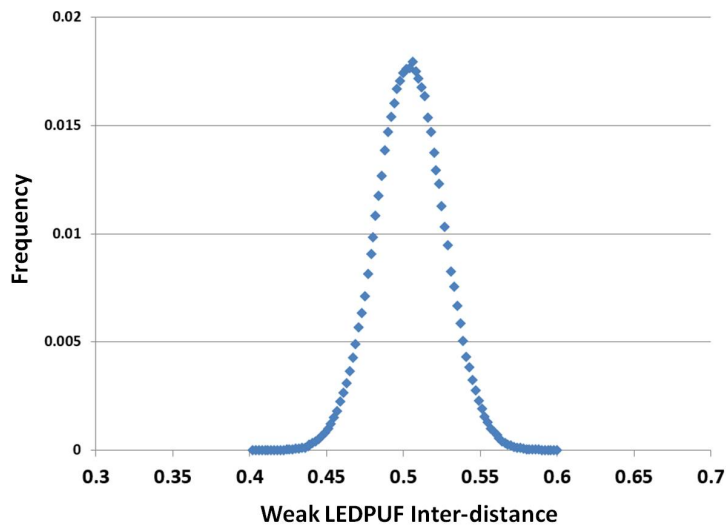
- A single bit-flip in the weak LEDPUF will cause a complete different strong LEDPUF response
- The intra-distance of a strong LEDPUF grows dramatically as the weak LEDPUF intra-distance increases



Uniqueness Evaluation

- 1000 weak/strong LEDPUFs are simulated
- Inter-distances are close to ideal **50%**

	Response Bits	Mean	Standard Deviation
Weak LEDPUF	512	50.3%	2%
Strong LEDPUF	256	50.0%	3%



Conclusion and Future Work

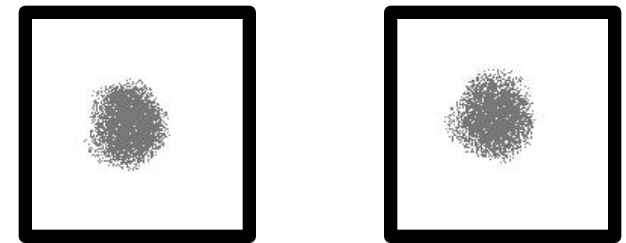
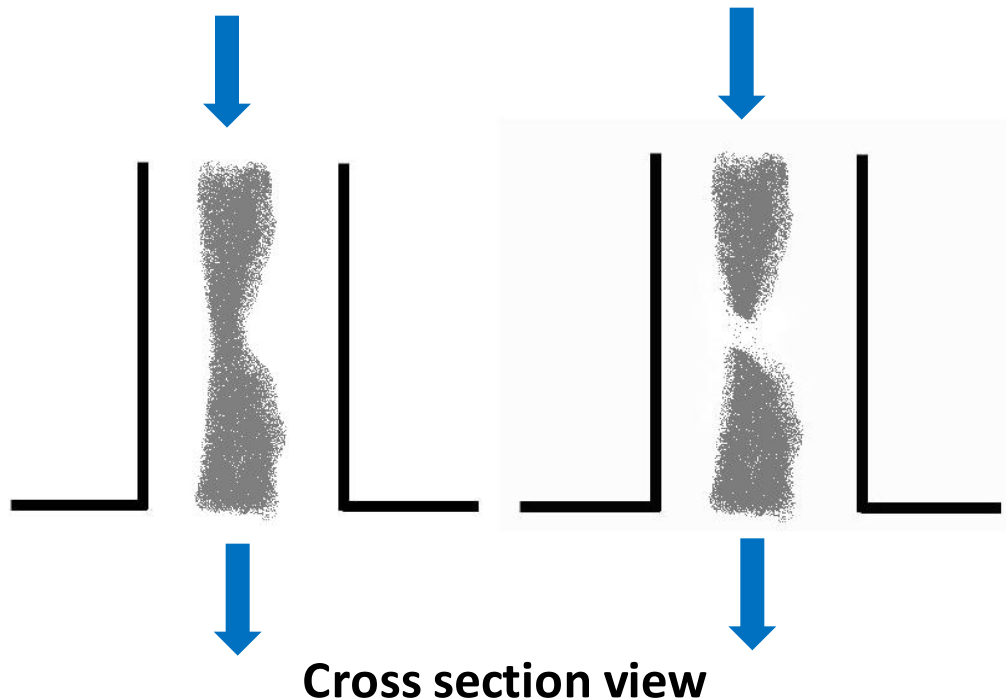
- **The first stability-guaranteed PUF is proposed**
 - Weak LEDPUF
 - Strong LEDPUF
- **Randomness extraction from locally enhanced DSA process**
- **Our future work includes**
 - Finding sources of LED that are
 - More **secure** than DSA
 - More **compatible** with existing CMOS technology
 - Developing a **quantitative security analysis** of stable/unstable PUF

Thank you!
Questions?

Backup Slides

Imaging Attack

- Cross section image ineffective because it destroys neighboring SSUs
- Top down image could be prevented by using a “tall” guiding template



Guess Work Analysis

- Probability mass function of a bit from 1500 DSA connections

$$p_X(1) = 0.4626 \quad p_X(0) = 0.5374$$

- Single round guessing attack

- min-entropy $H_{\min}(X) = -\log_2\left(\max_i p_i\right) = 0.8962$
- For a m-bit response, the success rate of a single guessing is $2^{-0.8962m}$
- With m=512 bits, the success rate is $\sim 0\%$

- Dictionary guessing attack

- Multiple guesses from the most probable response
- Shannon-entropy $H_{Sh}(x) = \sum_i -P_i \log_2(p_i) = 0.996$
- Number of expected attempts is lower-bounded by

$$E\{G\} \geq \frac{1}{4} 2^{mH_{Sh}(x)} = \frac{1}{4} 2^{0.996m}$$

- With m=512 bits, the expected attempts becomes unfeasibly large!

Guess Work Growth Rate

- Renyi entropy:

$$\lim_{m \rightarrow \infty} \frac{1}{m} \log_2 E \{G\} = H_{1/2}(X) = 2 \cdot \log_2 \left(\sum_i p_i^{1/2} \right) = 0.998$$

- $E \{G\}$ is upper bounded by $2^{0.998m}$ for a m-bit response
- **1.002m bits of LEDPUF = m bits fair coin tosses**